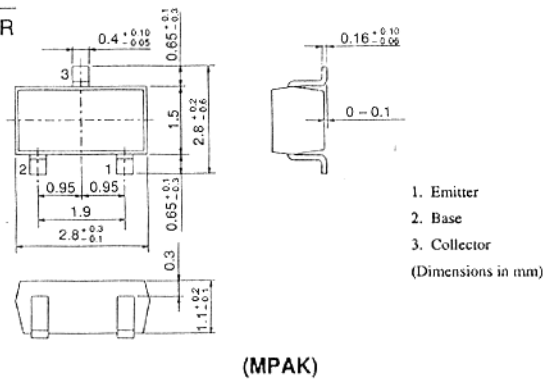


2SA1122

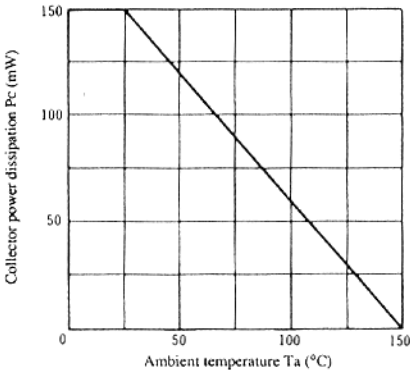
SILICON PNP EPITAXIAL
LOW FREQUENCY AMPLIFIER



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1122	Unit
Collector to base voltage	V _{CB0}	-55	V
Collector to emitter voltage	V _{CEO}	-55	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-55	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-55	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -30V, I _E = 0	—	—	-0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2V, I _C = 0	—	—	-0.5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	160	—	800	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA	—	—	-0.5	V
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	—	-0.75	V

* The 2SA1122 is grouped by h_{FE} as follows.

Grade	C	D	E
Mark	CC	CD	CE
h _{FE}	160 to 320	250 to 500	400 to 800

■ See characteristic curves of 2SA836.